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High density SiC for PVT[®]

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Development of high density, high purity SiC material for SiC crystal growth

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Nanomakers at a glance



A worldwide leader in industrial production (40t/year) of highquality high-purity silicon-based nanoparticles (nano-silicon and nano-silicon carbide) for the Semicon & Battery industries



Located in France (Rambouillet) with an internaional impact

- R&D, Sales & Production based in Paris (France)
- Subsidiary in Japan (in 2010)
- 99% of sales outside of Europe



International team of 16 employees, out of which 6 are in R&I

Active R&I activities

- R&I expenses represent more than 30% of our sales
- Patent families covering applications, products & processes.

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Nanomaker's R&I Activities

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- Previous experience with collaborative projects covering a variety of applications (Batteries, Ceramics Composites, others):
 - Partner of several Horizon 2020/Europe projects (including 2 on going)
 - Leader of 3 EIT Raw Materials projects
 - Leader of 2 French collaborative projects
- What sort of interaction exists with one of the 3IAs or other ETPs?
 - Experience as material supplier for semicon equipment parts producer
 - But new to this Semicon / chip ecosystem and associations
 - Recently applied to become a member of AENEAS

Collaboration Expectations



Collaborative project of interest to you	Chips JU, Horizon Europe, EIC accelerator
Scope	SiC source for SiC crystal growth by PVT
Project idea	To enhance the mass quantity of the SiC source by elevating its apparent density
Project impact	Higher productivity of SiC boule growth
Project consortium	Partner(s) in SiC PVT growth (equipment manufacturer, user) for co-development of ready to use solution
Other information (e.g. project budget, duration)	~ 2 years, budget depending on partner type

Nanomakers SiC source for PVT

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Solution development : high density Silicon Carbide

- High apparent SiC source density to increase the productivity of SiC boule growth
- Tunable Si/C ratio at nanoscale level
- 5.5N + available
- Nitrogen doping agent on demand

Partners for co-development projects

- Boule manufacturer for SiC source/process adaptation
- PVT equipment supplier for SiC source/equipment proposal